

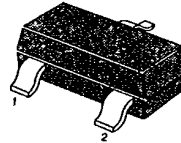
MMBC1623L3**NPN EPITAXIAL SILICON TRANSISTOR**

T-29-19-

AMPLIFIER TRANSISTOR**ABSOLUTE MAXIMUM RATINGS (T_a=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EB0}	5.0	V
Collector Current	I _C	100	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{stg}	150	°C

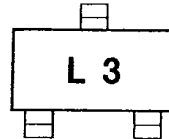
SOT-23



1. Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} =40V, I _E =0		100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} =5V, I _C =0		100	nA
DC Current Gain	h _{FE}	V _{CE} =6V, I _C =1.0mA	60	120	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C =100mA, I _B =10mA		0.3	V
Base-Emitter Saturation Voltage	V _{BE} (sat)	I _C =100mA, I _B =10mA		1.0	V
Base-Emitter On Voltage	V _{BE} (on)	I _C =1.0mA, V _{CE} =6V	0.6	0.7	V
Current Gain-Bandwidth Product	f _T	V _{CE} =6V, I _E =10mA f=100MHz	200		MHz

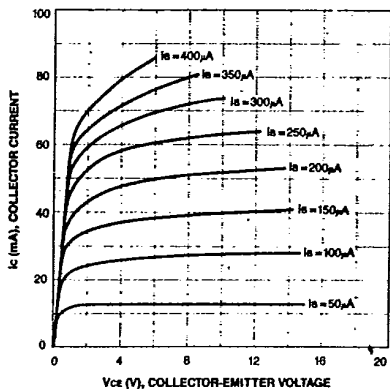
Marking

MMBC1623L3

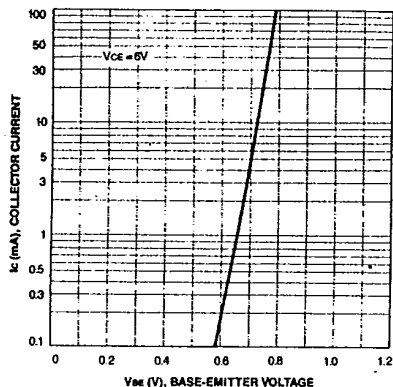
NPN EPITAXIAL SILICON TRANSISTOR

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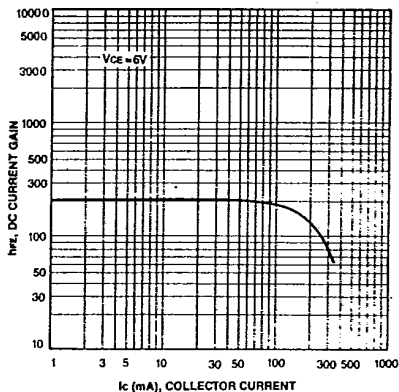
STATIC CHARACTERISTIC



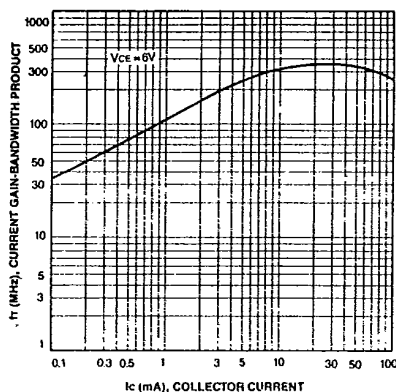
TRANSFER CHARACTERISTIC



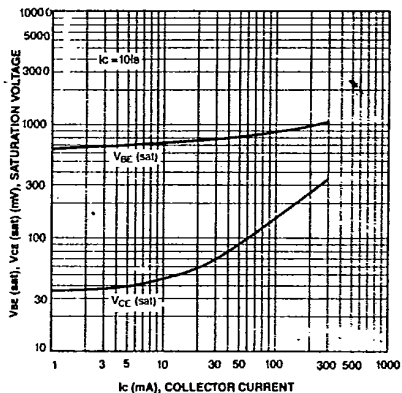
DC CURRENT GAIN



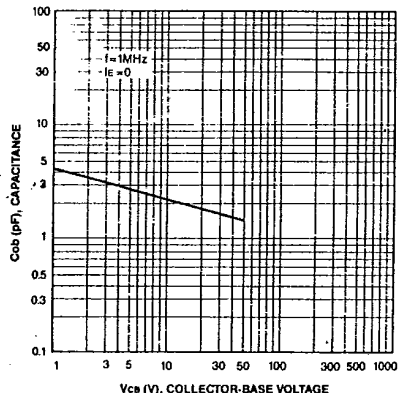
CURRENT GAIN BANDWIDTH PRODUCT



BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



OUTPUT CAPACITANCE



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